# 2SD1772, 2SD1772A

### Silicon NPN triple diffusion planar type

For power amplification

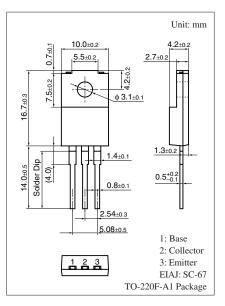
For TV vertical deflection output

#### Features

- $\bullet$  Large collector power dissipation  $P_{\rm C}$
- Full-pack package which can be installed to the heat sink with one screw

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Er	V <sub>CBO</sub>	200	V	
Collector-emitter voltage	2SD1772	V <sub>CEO</sub>	150	V
(Base open)	2SD1772A		180	
Emitter-base voltage (Coll	V <sub>EBO</sub>	6	V	
Collector current	I <sub>C</sub>	1	А	
Peak collector current	I <sub>CP</sub>	2	А	
Collector power dissipation		P <sub>C</sub>	25	W
	$T_a = 25^{\circ}C$		2.0	
Junction temperature	Tj	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	

#### Absolute Maximum Ratings $T_C = 25^{\circ}C$



#### Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

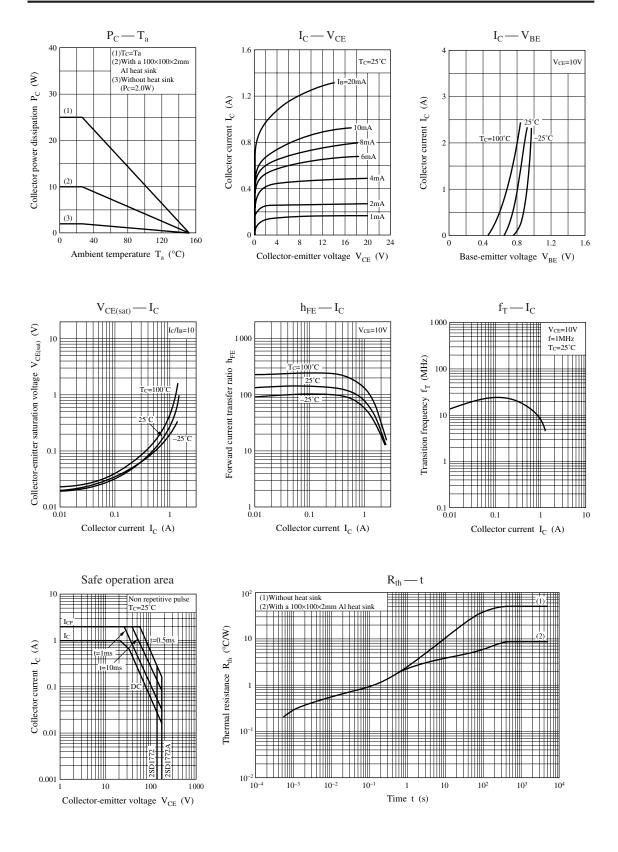
Parameter		Symbol	Conditions	Min	Тур	Max	Unit
Collector-emitter voltage	2SD1772	V <sub>CEO</sub>	$I_{\rm C} = 5  {\rm mA},  I_{\rm B} = 0$	150			V
(Base open)	2SD1772A			180			
Emitter-base voltage (Colle	ctor open)	V <sub>EBO</sub>	$I_{\rm E} = 0.5 \text{ mA}, I_{\rm C} = 0$	6			V
Base-emitter voltage		V <sub>BE</sub>	$V_{CE} = 10 \text{ V}, I_C = 300 \text{ mA}$			1.0	V
Collector-base cutoff current (Emitter open)		I <sub>CBO</sub>	$V_{CB} = 200 \text{ V}, I_E = 0$			50	μΑ
Emitter-base cutoff current (Collector open)		I <sub>EBO</sub>	$V_{EB} = 4 V, I_C = 0$			50	μΑ
Forward current transfer rat	io	h <sub>FE1</sub> *	$V_{CE} = 10 \text{ V}, I_{C} = 100 \text{ mA}$	60		240	_
		h <sub>FE2</sub>	$V_{CE} = 10 \text{ V}, I_C = 300 \text{ mA}$	50			
Collector-emitter saturation	voltage	V <sub>CE(sat)</sub>	$I_{\rm C} = 500 \text{ mA}, I_{\rm B} = 50 \text{ mA}$			1.0	V
Transition frequency		f <sub>T</sub>	$V_{CE} = 10 \text{ V}, I_C = 0.1 \text{ A}, f = 1 \text{ MHz}$		20		MHz
Collector output capacitance		C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		27		pF
(Common base, input open	circuited)						

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*: Rank classification

Rank	Q	Р		
$h_{\rm FE1}$	60 to 140	100 to 240		

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